

Oral presentation | 13 Semiconductors | 13.7 Compound and power electron devices and process technology

[19p-CE-5~17]13.7 Compound and power electron devices and process technology

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Wed. Sep 19, 2018 3:00 PM - 6:45 PM CE (Century Hall)

△ : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼ : Both of Above

No Mark : None of Above

3:00 PM - 3:30 PM

[19p-CE-5][JSAP Paper Award Speech] Hydride-vapor-phase epitaxial growth of highly pure GaN layers with smooth as-grown surfaces on freestanding GaN substrates

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Keywords:JSAP Paper Award